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# ACTT4X-800C

## AC Thyristor Triac power switch

15 August 2014

Product data sheet

## 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

## 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 20 \text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	35	A
$T_j$	junction temperature		-	-	125	$^\circ\text{C}$
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_h \leq 94^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	4	A



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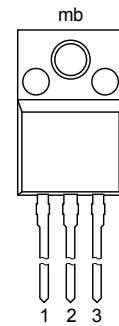
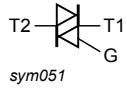
## ACTT4X-800C

### AC Thyristor Triac power switch

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{PP}$	peak pulse voltage	$T_j = 25^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>		-	-	2	kV
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25^\circ\text{C}$	850	-	-	-	V
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>		1000	-	-	V/ $\mu\text{s}$
$dl_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated	 <b>TO-220F (SOT186A)</b>	 <b>sym051</b>

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
		Name	Description
ACTT4X-800C	TO-220F		plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

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## ACTT4X-800C

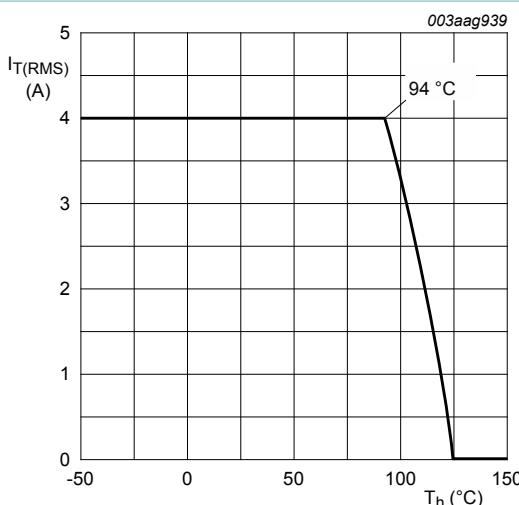
### AC Thyristor Triac power switch

## 7. Limiting values

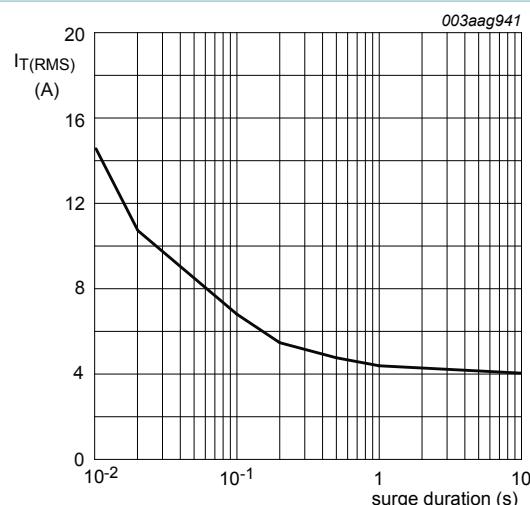
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 94^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	35	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$	-	39	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	6	$\text{A}^2\text{s}$
$dI_T/dt$	rate of rise of on-state current	$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$
$V_{PP}$	peak pulse voltage	$T_j = 25^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



$f = 50\text{ Hz}; T_h = 94^\circ\text{C}$

**Fig. 2. on-state current as a function of surge duration; maximum values**

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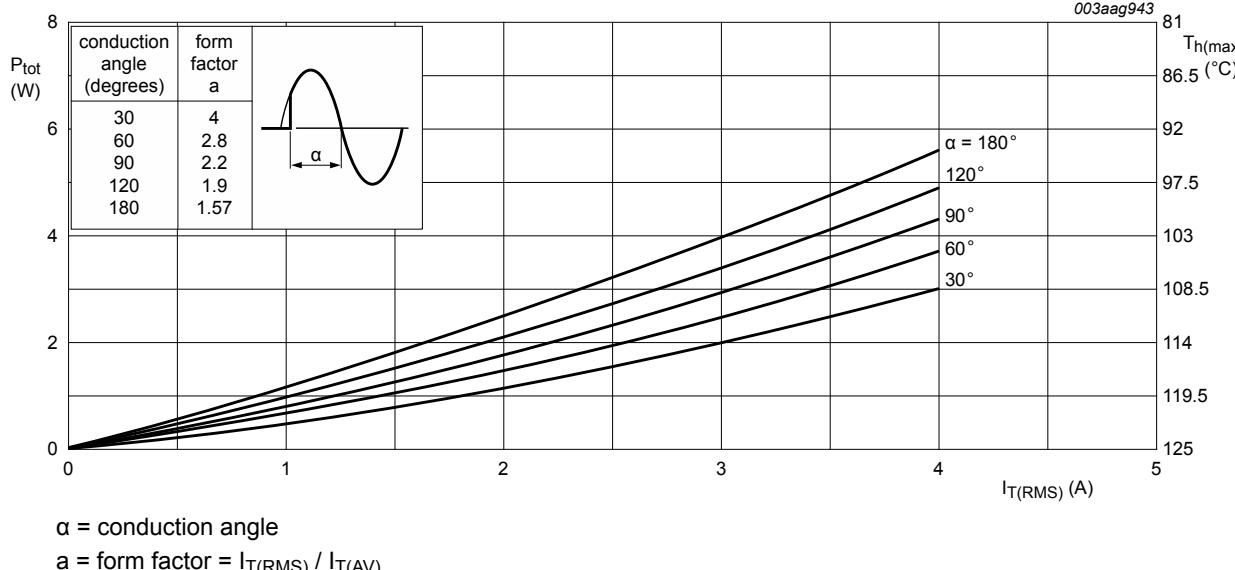


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

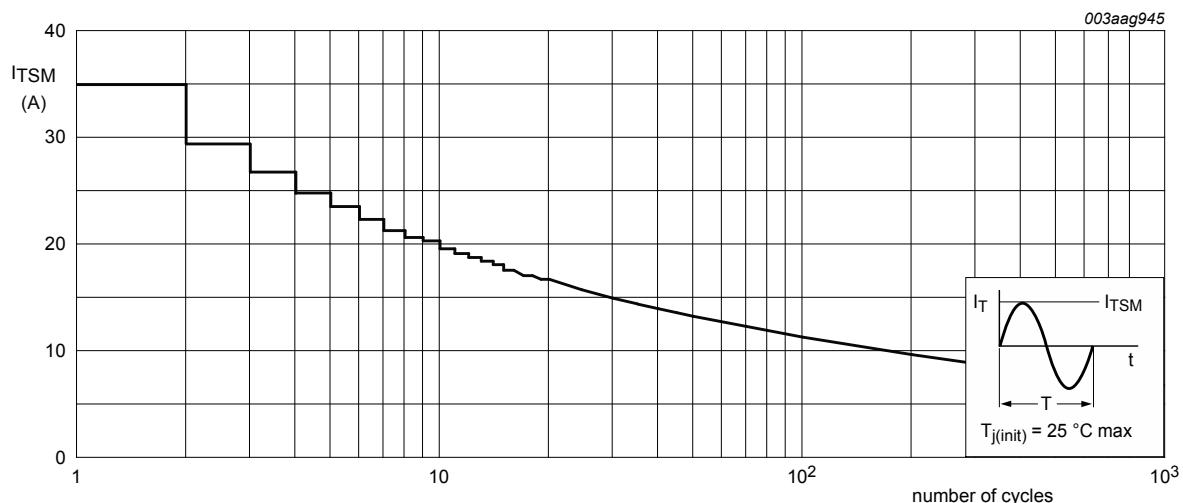


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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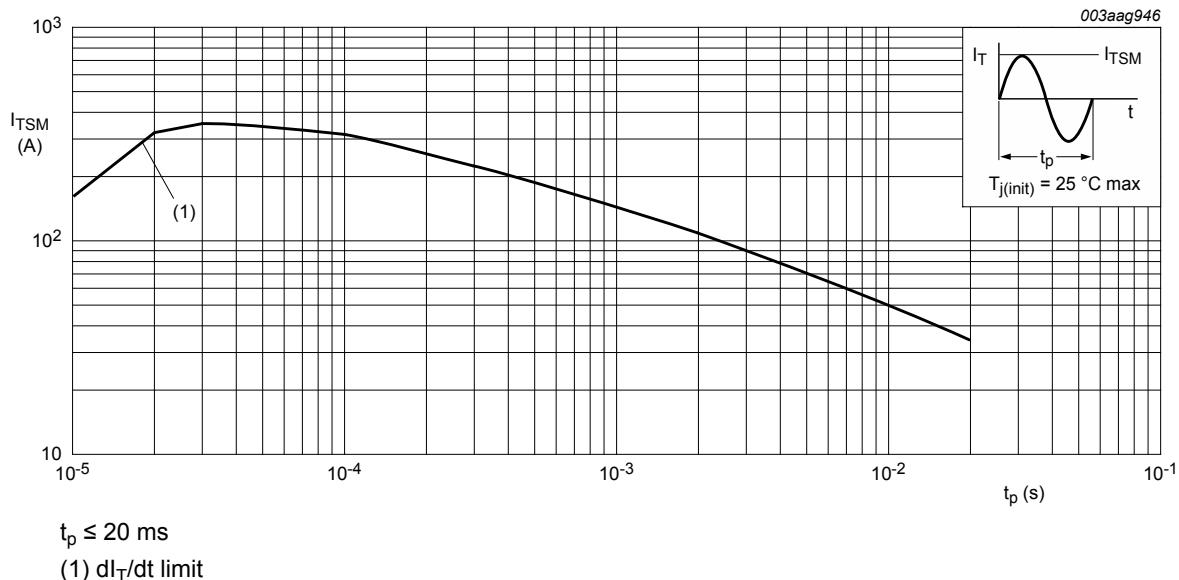


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

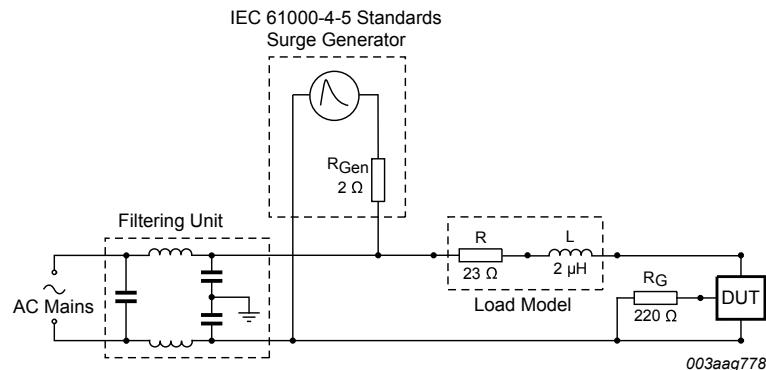


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

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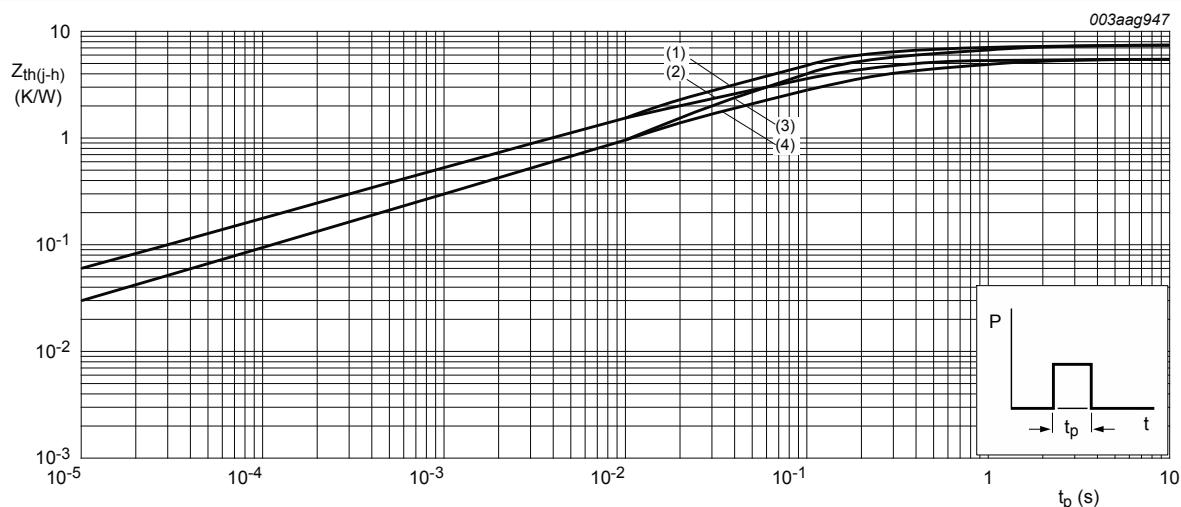
## ACTT4X-800C

AC Thyristor Triac power switch

## 8. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; <a href="#">Fig. 7</a>	-	-	5.5	K/W
		full cycle or half cycle; without heatsink compound; <a href="#">Fig. 7</a>				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

**Fig. 7. Transient thermal impedance from junction to heatsink as a function of pulse width**

## 9. Isolation characteristics

**Table 6. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	$50 \text{ Hz} \leq f \leq 60 \text{ Hz}$ ; $RH \leq 65\% \text{ RH}$ ; $T_h = 25^\circ \text{C}$ ; from all terminals to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
$C_{isol}$	isolation capacitance	$f = 1 \text{ MHz}$ ; $T_h = 25^\circ \text{C}$ ; from main terminal 2 to external heatsink	-	10	-	pF

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## 10. Characteristics

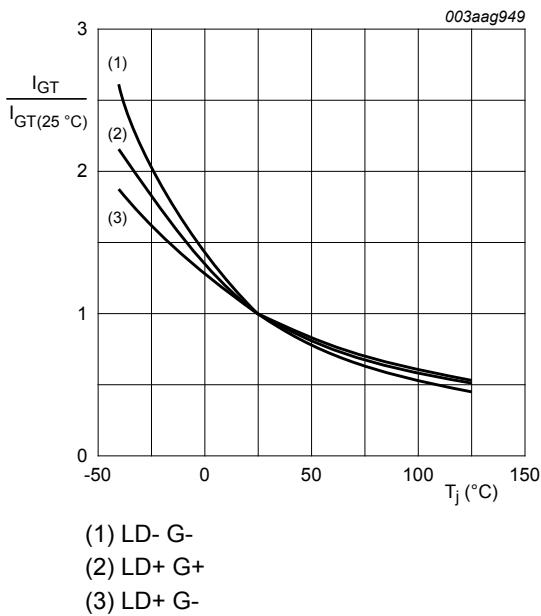
**Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD+ G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD+ G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD- G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
$I_L$	latching current	$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD+ G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	50	mA
		$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD+ G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	60	mA
		$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD- G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	50	mA
$I_H$	holding current	$V_D = 12 \text{ V}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	-	35	mA
$V_T$	on-state voltage	$I_T = 6 \text{ A}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	-	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 12</a>		-	0.8	1	V
		$V_D = 400 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; $T_j = 125^\circ\text{C}$ ; <a href="#">Fig. 12</a>		0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800 \text{ V}$ ; $T_j = 25^\circ\text{C}$		-	-	10	$\mu\text{A}$
		$V_D = 800 \text{ V}$ ; $T_j = 125^\circ\text{C}$		-	-	0.5	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1 \text{ mA}$ ; $t_p = 1 \text{ ms}$ ; $T_j = 25^\circ\text{C}$		850	-	-	V
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536 \text{ V}$ ; $T_j = 125^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>		1000	-	-	$\text{V}/\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400 \text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $I_{T(\text{RMS})} = 4 \text{ A}$ ; $dV_{com}/dt = 20 \text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		8	-	-	$\text{A}/\text{ms}$
		$V_D = 400 \text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $I_{T(\text{RMS})} = 4 \text{ A}$ ; $dV_{com}/dt = 10 \text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 16</a> ; <a href="#">Fig. 15</a>		10	-	-	$\text{A}/\text{ms}$
		$V_D = 400 \text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $I_{T(\text{RMS})} = 4 \text{ A}$ ; $dV_{com}/dt = 1 \text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		15	-	-	$\text{A}/\text{ms}$

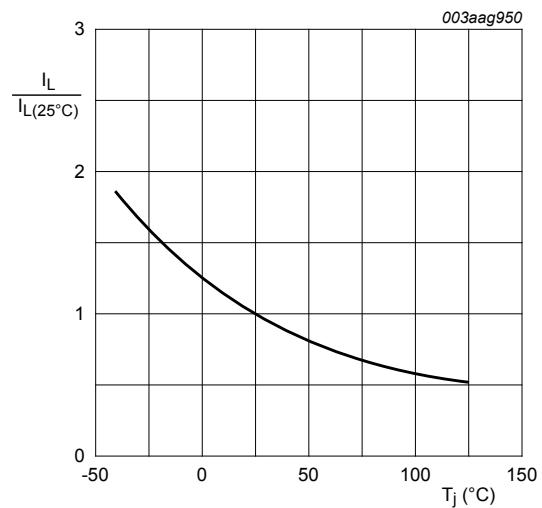
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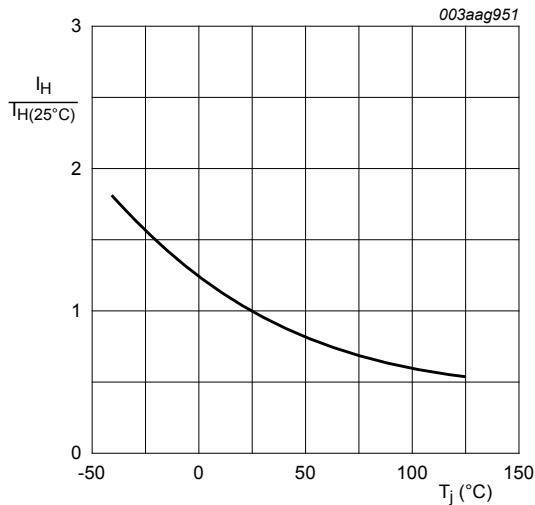
### AC Thyristor Triac power switch



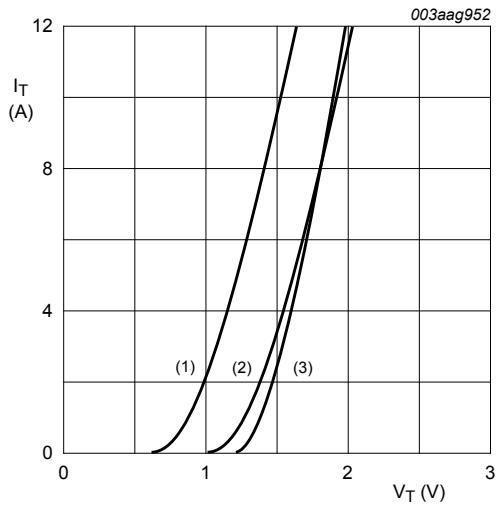
**Fig. 8.** Normalized gate trigger current as a function of junction temperature



**Fig. 9.** Normalized latching current as a function of junction temperature



**Fig. 10.** Normalized holding current as a function of junction temperature



$$V_0 = 1.242 \text{ V}; R_s = 0.074 \Omega$$

(1)  $T_j = 125^{\circ}\text{C}$ ; typical values

(2)  $T_j = 125^{\circ}\text{C}$ ; maximum values

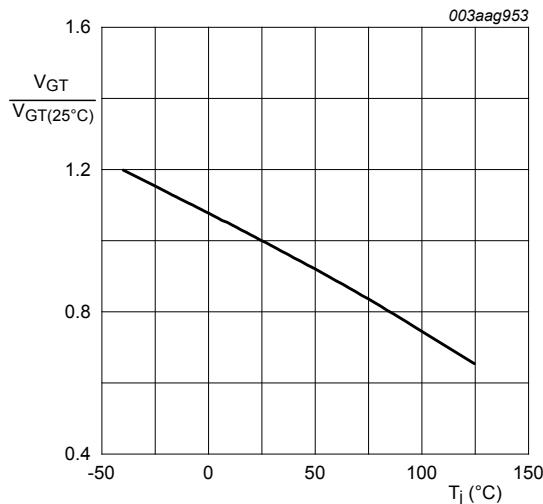
(3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

**Fig. 11.** On-state current as a function of on-state voltage

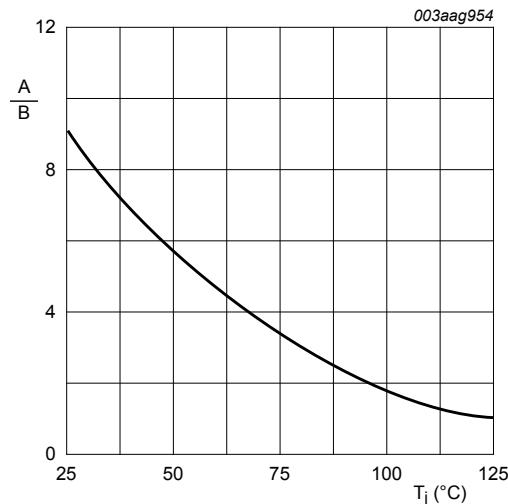
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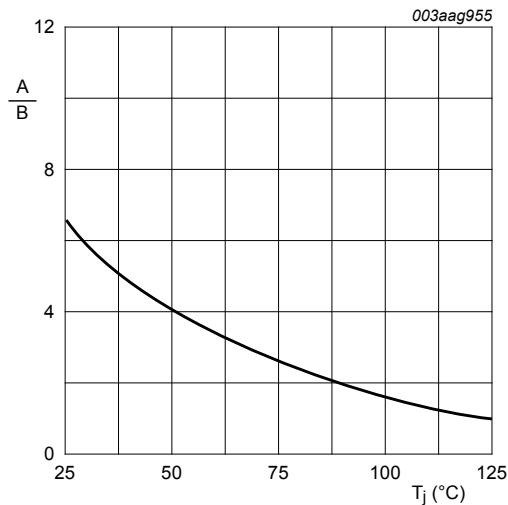


**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**



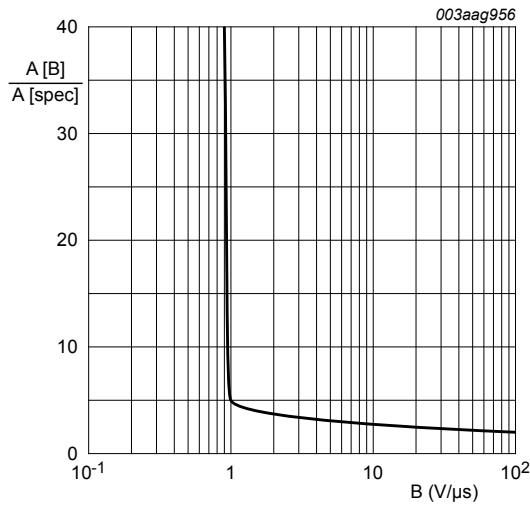
$A = dV_D/dt$  at condition  $T_j$  °C  
 $B = dV_D/dt$  at condition  $T_j$  [125] °C

**Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature**



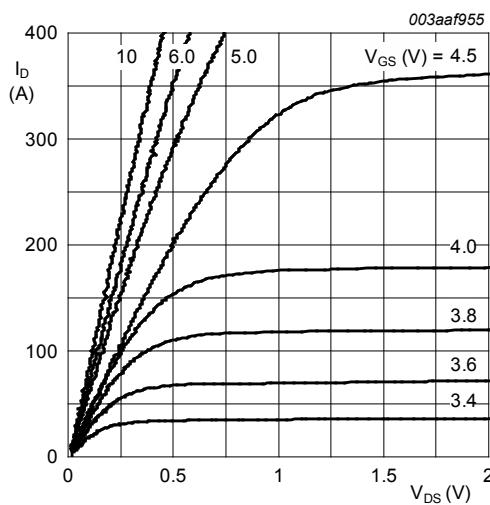
$A = dI_{com}/dt$  at condition  $T_j$  °C  
 $B = dI_{com}/dt$  at condition  $T_j$  [125] °C  
 $V_D = 400$  V

**Fig. 14. Normalized critical rate of rise of commuting current as a function of junction temperature**



$A[B]$  is  $dI_{com}/dt$  at condition B,  $dV_{com}/dt$   
 $A[\text{spec}]$  is the specified data sheet value of  $dI_{com}/dt$  turn-off time < 20 ms

**Fig. 15. Normalized critical rate of change of commuting current as a function of critical rate of change of commuting voltage; minimum values**

**NXP Semiconductors****ACTT4X-800C****AC Thyristor Triac power switch** $T_j = 25^\circ\text{C}$ ;  $t_p = 300 \mu\text{s}$ **Fig. 16. Output characteristics: drain current as a function of drain-source voltage; typical values**

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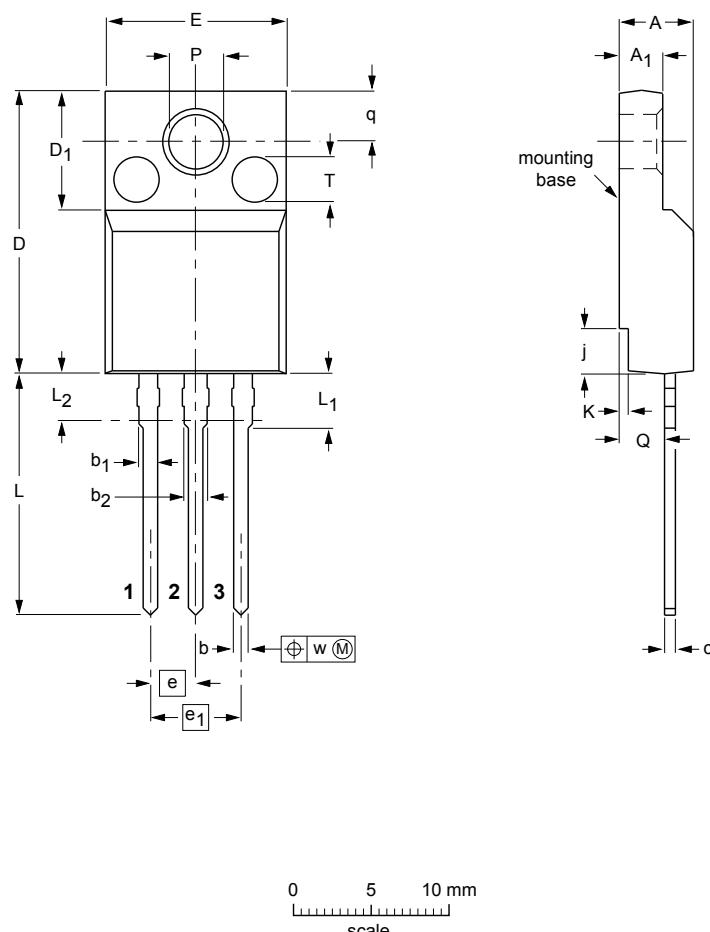
## ACTT4X-800C

AC Thyristor Triac power switch

### 11. Package outline

Plastic single-ended package; isolated heatsink mounted;  
 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



#### DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j	K	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	T <sup>(2)</sup>	w
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	2.5	0.4
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7	2.54	5.08	1.7	0.4	13.5	2.79	3.0	3.0	2.3	2.6	2.5	0.4

#### Notes

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are # 2.5 x 0.8 max. depth

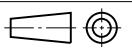
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				-02-04-09-06-02-14

Fig. 17. Package outline TO-220F (SOT186A)

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## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## ACTT4X-800C

### AC Thyristor Triac power switch

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